74LVC38A

Quad 2-input NAND gate; open-drain Rev. 4 — 4 November 2011

Product data sheet

1. **General description**

The 74LVC38A provides four 2-input NAND functions. The outputs are open-drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V applications.

Features and benefits 2.

- 5 V tolerant inputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 V to 5.5 V
- CMOS low power consumption
- Direct interface with TTL levels
- Open-drain outputs
- Complies with JEDEC standard:
 - ◆ JESD8-7A (1.65 V to 1.95 V
 - JESD8-5A (2.3 V to 2.7 V
 - ◆ JESD8-C/JESD36 (2.7 V to 3.6 V
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115B exceeds 200 V
 - ◆ CDM JESD22-C101E exceeds 1000 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Ordering information 3.

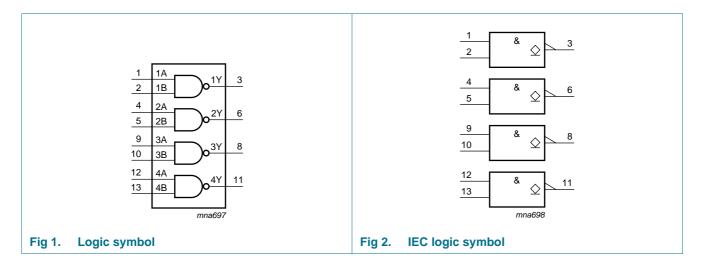
Table 1. **Ordering information**

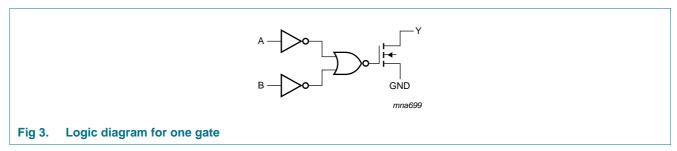
Type number	Package	Package										
	Temperature range	Name	Description	Version								
74LVC38AD	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1								
74LVC38ADB	–40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1								
74LVC38APW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1								
74LVC38ABQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 \times 3 \times 0.85 mm	SOT762-1								



Quad 2-input NAND gate; open-drain

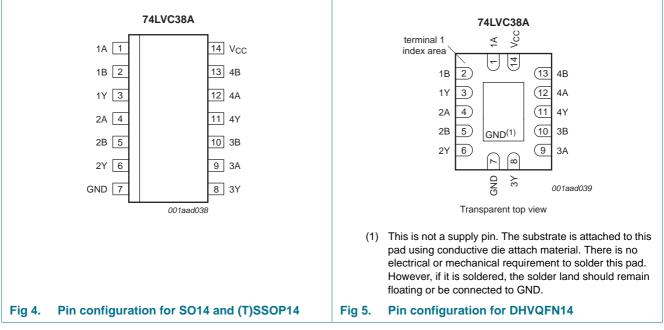
4. Functional diagram





5. Pinning information

5.1 Pinning



74LVC38A

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5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A, 2A, 3A, 4A	1, 4, 9, 12	data input
1B, 2B, 3B, 4B	2, 5, 10, 13	data input
1Y, 2Y, 3Y, 4Y	3, 6, 8, 11	data output
GND	7	ground (0 V)
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function selection[1]

Input					
nA	nB	nY			
L	L	Z			
L	Н	Z			
Н	L	Z			
Н	Н	L			

^[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
l _{OK}	output clamping current	V _O < 0	-50	-	mA
Vo	output voltage	active mode	<u>[2]</u> −0.5	+6.5	V
		high-impedance mode	<u>[2]</u> −0.5	+6.5	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	50	mA
I _{CC}	supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[3]</u> _	500	mW

^[1] The minimum input voltage ratings may be exceeded if the input current ratings are observed.

^[2] The output voltage ratings may be exceeded if the output current ratings are observed.

^[3] For SO14 packages: above 70 °C the value of P_{tot} derates linearly with 8 mW/K. For (T)SSOP14 packages: above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K. For DHVQFN14 packages: above 60 °C the value of P_{tot} derates linearly with 4.5 mW/K.

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8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
		functional	1.2	-	-	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	active mode	0	-	V_{CC}	V
		high-impedance mode	0	-	5.5	V
T _{amb}	ambient temperature	in free air	-40	-	+125	°C
Δt/ΔV	input transition rise and fall	V _{CC} = 1.65 V to 2.7 V	0	-	20	ns/V
	rate	V _{CC} = 2.7 V to 3.6 V	0	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	-40 °C to	+125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level	V _{CC} = 1.2 V	1.08	-	-	1.08	-	V
	input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	$0.65 \times V_{CC}$	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2.0	-	-	2.0	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	$0.7 \times V_{CC}$	-	V
V_{IL}	LOW-level input	V _{CC} = 1.2 V	-	-	0.12	-	0.12	V
	voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.30 \times V_{CC}$	-	$0.30 \times V_{CC}$	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}						
		$I_O = 100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	-	0.20	-	0.3	V
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	-	0.65	V
		$I_O = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.6	-	0.8	V
		$I_O = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	-	0.6	V
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	0.8	V
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	-	0.8	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 1.65 V to 5.5 V	-	±0.1	±5	-	±20	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$; $V_O = 5.5 \text{ V or GND}$; $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	0.1	±5	-	±20	μΑ
l _{OFF}	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	±0.1	±10	-	±20	μА

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	-40 °C to	+125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	0.1	10	-	40	μΑ
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A};$ $V_{CC} = 2.7 \text{ V to } 5.5 \text{ V}$	-	5	500	-	5000	μА
C _I	input capacitance	$V_{CC} = 0 \text{ V to 5.5 V};$ $V_{I} = \text{GND to V}_{CC}$	-	4.0	-	-	-	pF

^[1] All typical values are measured at V_{CC} = 3.3 V (unless stated otherwise) and T_{amb} = 25 °C.

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V). For test circuit see Figure 7.

Symbol	Parameter	Conditions	-4	0 °C to +8	5 °C	–40 °C to	+125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
t_{PZL}	OFF-state to LOW	nA, nB to nY; see Figure 6						
	propagation delay	$V_{CC} = 1.2 \text{ V}$	-	5.7	-	-	-	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.0	2.6	6.0	1.0	6.9	ns
	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.5	1.8	3.3	0.5	3.8	ns	
		$V_{CC} = 2.7 \text{ V}$	0.5	1.7	2.9	0.5	4.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0.5	1.8	3.0	0.5	4.0	ns
t _{PLZ}	LOW to OFF-state	nA, nB to nY; see Figure 6						
	propagation delay	$V_{CC} = 1.2 \text{ V}$	-	5.7	-	-	-	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1.0	2.7	6.0	1.0	6.9	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0.5	1.5	3.3	0.5	3.8	ns
		$V_{CC} = 2.7 \text{ V}$	1.0	2.6	3.8	1.0	5.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.3	3.6	1.0	4.5	ns
t _{sk(o)}	output skew time		[2] _	-	1.0	-	1.5	ns

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 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V). For test circuit see <u>Figure 7</u>.

Symbol	Parameter	Conditions		-40	°C to +8	5 °C	–40 °C to	-40 °C to +125 °C		
				Min	Typ[1]	Max	Min	Max		
C _{PD} power dissipation capacitance	per gate; $V_I = GND$ to V_{CC}	[3]		'	'	'		'		
	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	6.2	-	-	-	pF		
	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	9.7	-	-	-	pF		
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	12.9	-	-	-	pF	

- [1] Typical values are measured at $T_{amb} = 25$ °C and $V_{CC} = 1.2$ V, 1.8 V, 2.5 V, 2.7 V, and 3.3 V respectively.
- [2] Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$

f_i = input frequency in MHz; f_o = output frequency in MHz

C_L = output load capacitance in pF

V_{CC} = supply voltage in Volts

N = number of inputs switching

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs

11. AC waveforms

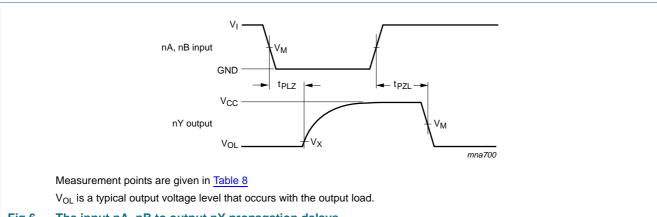
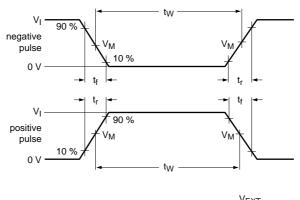


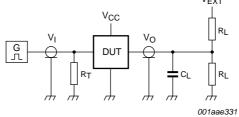
Fig 6. The input nA, nB to output nY propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
V _{CC}	V _M	V _X
<2.7 V	$0.5 \times V_{CC}$	V _{OL} + 0.15 V
≥2.7 V to 3.6 V	1.5 V	V _{OL} + 0.3 V

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Test data is given in Table 9.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 7. Test circuit for measuring switching times

Table 9. Test data

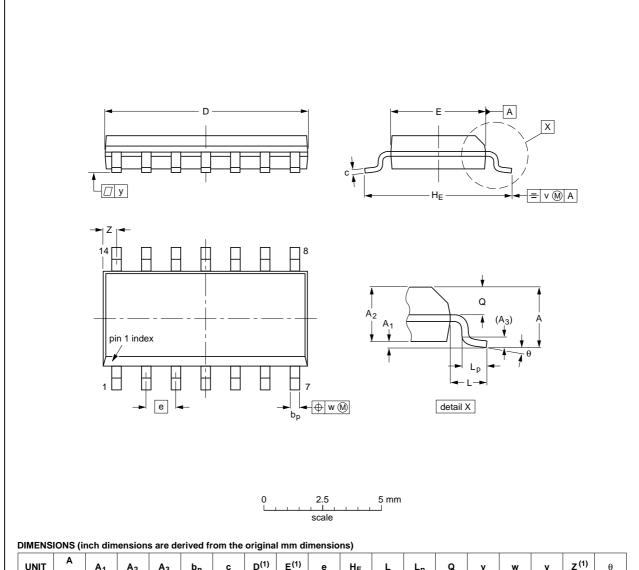
Supply voltage	Input		Load		V _{EXT}	V _{EXT}		
	Vı	t _r , t _f	CL	R _L	t _{PLH} , t _{PHL}	t _{PLZ} , t _{PZL}		
1.2 V	V _{CC}	≤ 2 ns	30 pF	1 kΩ	open	$2\times V_{CC}$		
1.65 V to 1.95 V	V _{CC}	≤ 2 ns	30 pF	1 kΩ	open	$2\times V_{CC}$		
2.3 V to 2.7 V	V _{CC}	≤ 2 ns	30 pF	500 Ω	open	$2\times V_{CC}$		
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open	$2\times V_{CC}$		
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	$500~\Omega$	open	$2\times V_{CC}$		

Quad 2-input NAND gate; open-drain

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.35 0.34	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC JEDEC		JEITA		PROJECTION	ISSUE DATE	
SOT108-1	076E06	MS-012				99-12-27 03-02-19	

Fig 8. Package outline SOT108-1 (SO14)

74LVC38A

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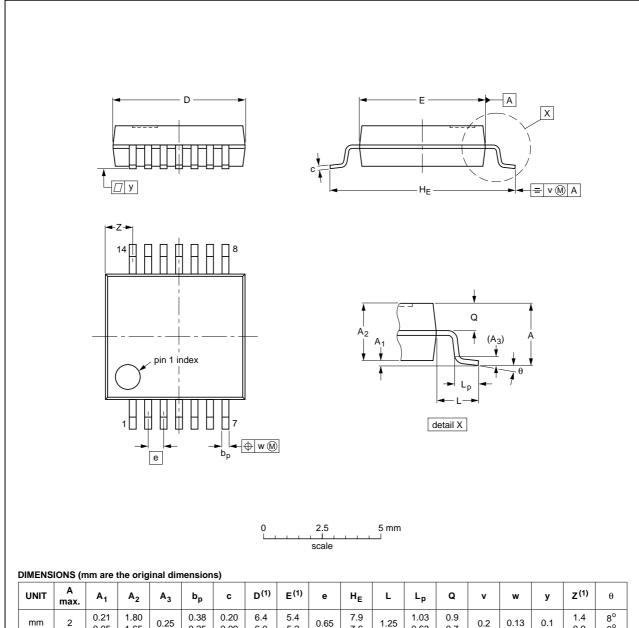
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Quad 2-input NAND gate; open-drain

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



							-,												
UN	TIV	A max.	A ₁	A ₂	A ₃	b _p	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
m	ım	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT337-1		MO-150			99-12-27 03-02-19

Package outline SOT337-1 (SSOP14) Fig 9.

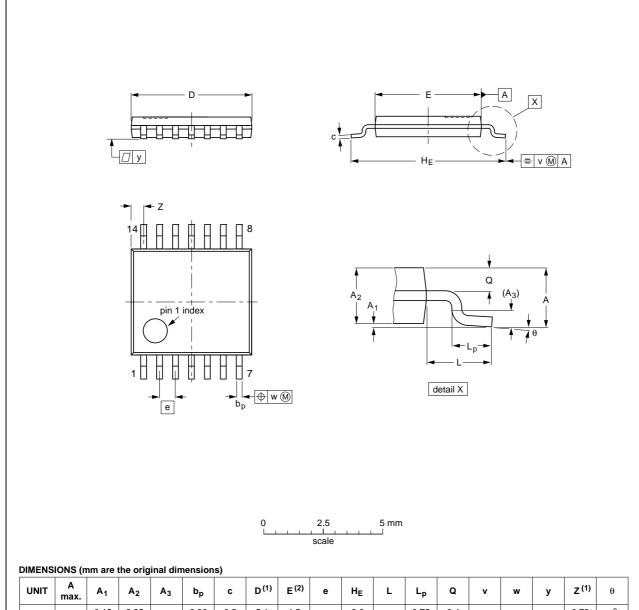
74LVC38A

74LVC38A NXP Semiconductors

Quad 2-input NAND gate; open-drain

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



	•					•												
UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT402-1		MO-153			99-12-27 03-02-18	
						-

Fig 10. Package outline SOT402-1 (TSSOP14)

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74LVC38A

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

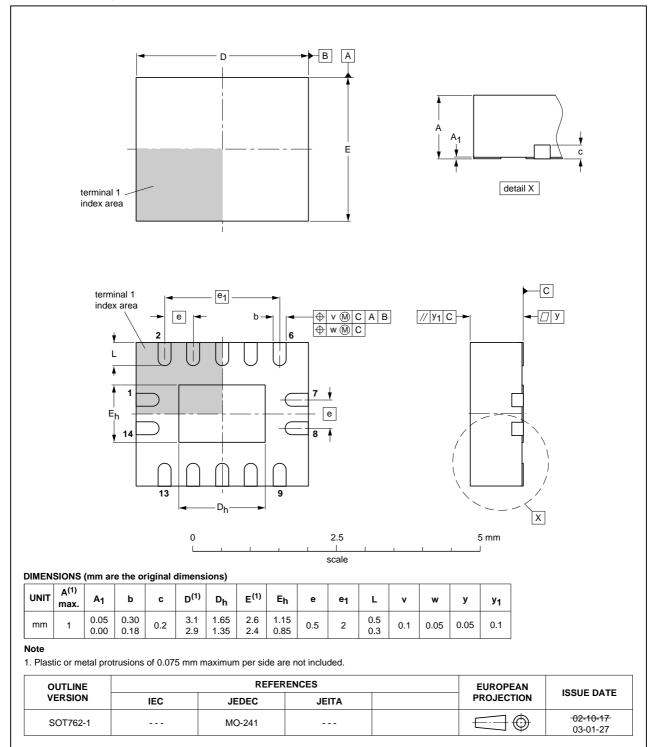


Fig 11. Package outline SOT762-1 (DHVQFN14)

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Quad 2-input NAND gate; open-drain

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC38A v.4	20111104	Product data sheet	-	74LVC38A v.3
Modifications:	 The format of NXP Semicon 	this document has been redeaductors.	signed to comply with t	he new identity guidelines of
	 Legal texts ha 	ve been adapted to the new	company name where	appropriate.
	• <u>Table 4</u> , <u>Table</u>	5, Table 6, Table 7 and Table	8: values added for lo	ower voltage ranges.
74LVC38A v.3	20040322	Product specification	-	74LVC38A v.2
74LVC38A v.2	20040310	Product specification	-	74LVC38A v.1
74LVC38A v.1	20020408	-	-	-
-				

Quad 2-input NAND gate; open-drain

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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